

CD74HC86, CD74HCT86

High Speed CMOS Logic Quad 2-Input EXCLUSIVE OR Gate

Features

- Typical Propagation Delay: 9ns at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^\circ C$
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . $-55^\circ C$ to $125^\circ C$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V$ (Max), $V_{IH} = 2V$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

Applications

- Logical Comparators
- Parity Generators and Checkers
- Adders and Subtractors

Description

The Harris CD74HC86, CD74HCT86 contain four independent EXCLUSIVE OR gates in one package. They provide the system designer with a means for implementation of the EXCLUSIVE OR function. Logic gates utilize silicon gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 74HCT logic family is functionally pin compatible with the standard 74LS logic family.

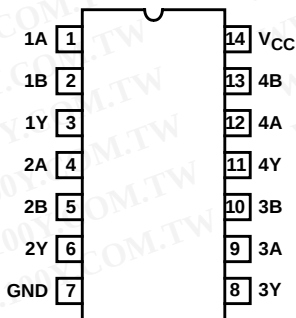
Ordering Information

PART NUMBER	TEMP. RANGE ($^\circ C$)	PACKAGE	PKG. NO.
CD74HC86E	-55 to 125	14 Ld PDIP	E14.3
CD74HCT86E	-55 to 125	14 Ld PDIP	E14.3
CD74HC86M	-55 to 125	14 Ld SOIC	M14.15
CD74HCT86M	-55 to 125	14 Ld SOIC	M14.15
CD54HC86W	-55 to 125	Wafer	
CD54HCT86W	-55 to 125	Wafer	
CD54HC86H	-55 to 125	Die	

NOTE: When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.

Pinout

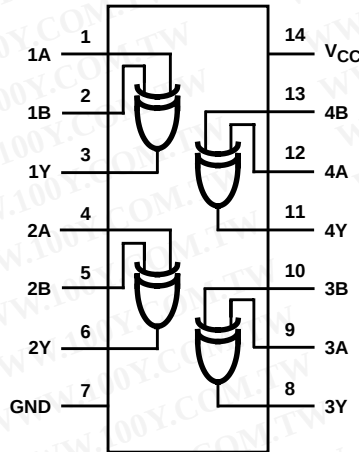
CD74HC86, CD74HCT86
(PDIP, SOIC)
TOP VIEW



CD74HC86, CD74HCT86

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Functional Diagram

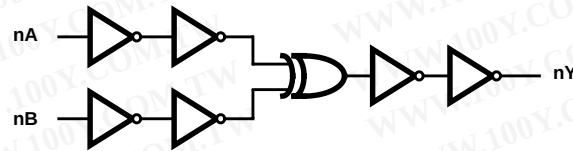


TRUTH TABLE

INPUTS		OUTPUT
nA	nB	nY
L	L	L
L	H	H
H	L	H
H	H	L

NOTE: H = High Voltage Level, L = Low Voltage Level

Logic Symbol



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Absolute Maximum Ratings

DC Supply Voltage, V_{CC} -0.5V to 7V
 DC Input Diode Current, I_{IK}
 For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ $\pm 20mA$
 DC Output Diode Current, I_{OK}
 For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ $\pm 20mA$
 DC Output Source or Sink Current per Output Pin, I_O
 For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ $\pm 25mA$
 DC V_{CC} or Ground Current, I_{CC} or I_{GND} $\pm 50mA$

Thermal Information

Thermal Resistance (Typical, Note 1) θ_{JA} ($^{\circ}C/W$)
 PDIP Package 100
 SOIC Package 180
 Maximum Junction Temperature $150^{\circ}C$
 Maximum Storage Temperature Range $-65^{\circ}C$ to $150^{\circ}C$
 Maximum Lead Temperature (Soldering 10s) $300^{\circ}C$
 (SOIC - Lead Tips Only)

Operating Conditions

Temperature Range (T_A) $-55^{\circ}C$ to $125^{\circ}C$
 Supply Voltage Range, V_{CC}
 HC Types 2V to 6V
 HCT Types 4.5V to 5.5V
 DC Input or Output Voltage, V_I , V_O 0V to V_{CC}
 Input Rise and Fall Time
 2V 1000ns (Max)
 4.5V 500ns (Max)
 6V 400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO +85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	6	-	-	2	-	20	-	40	µA

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DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO +85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	-0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	2	-	20	-	40	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 2)	ΔI _{CC}	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE:

- For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
All	1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g. 360μA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay, Input to Output (Figure 1)	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	120	-	150	-	180	ns
			4.5	-	-	24	-	30	-	36	ns
			6	-	-	20	-	26	-	31	ns
Propagation Delay, Data Input to Output Y	t _{PLH} , t _{PHL}	C _L = 15pF	5	-	9	-	-	-	-	-	ns
Transition Times (Figure 1)	t _{TLH} , t _{THL}	C _L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns

Switching Specifications Input $t_r, t_f = 6\text{ns}$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Input Capacitance	C_I	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	22	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay, Input to Output (Figure 2)	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	-	32	-	40	-	48	ns
Propagation Delay, Data Input to Output Y	t_{PLH}, t_{PHL}	$C_L = 15\text{pF}$	5	-	13	-	-	-	-	-	ns
Transition Times (Figure 2)	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C_I	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	27	-	-	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per gate.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = input frequency, C_L = output load capacitance, V_{CC} = supply voltage.

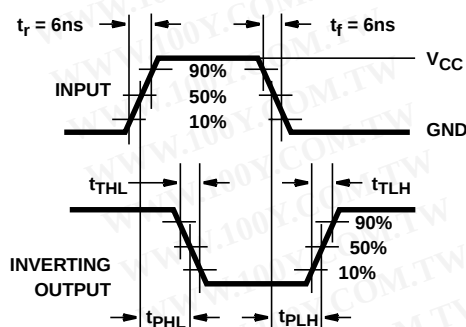
Test Circuits and Waveforms


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

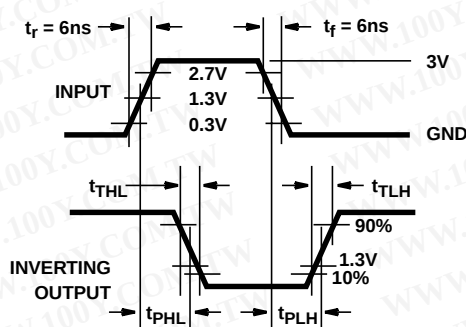


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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